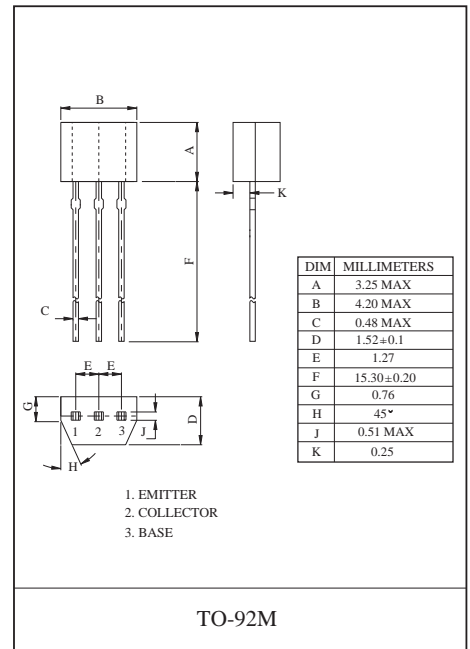


FTA1267 TRANSISTOR (PNP)

FEATURES

- High DC Current Gain
- Complementary to FTC3199



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector- Base Voltage	- 50	V
V _{CEO}	Collector- Emitter Voltage	- 50	V
V _{EBO}	Emitter- Base Voltage	- 5	V
I _C	Collector Current - Continuous	- 0.15	A
P _C	Collector Power Dissipation	0.4	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	- 55- 150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{(BR)CBO}	I _C =- 100μA, I _E =0	- 50			V
Collector- emitter breakdown voltage	V _{(BR)CEO}	I _C =- 1mA, I _B =0	- 50			V
Emitter- base breakdown voltage	V _{(BR)EBO}	I _E =- 100μA, I _C =0	- 5			V
Collector cut- off current	I _{CBO}	V _{CB} =- 50V, I _E =0			- 0.1	μA
Emitter cut- off current	I _{EBO}	V _{EB} =- 5V, I _C =0			- 0.1	μA
DC current gain	h _{FE}	V _{CE} =- 6V, I _C =- 2mA	70		400	
Collector- emitter saturation voltage	V _{CE(sat)}	I _C =- 100mA, I _B =- 10mA			- 0.25	V
Transition frequency	f _T	V _{CE} =- 10V, I _C =- 1mA, f=30MHz	80			MHz
Collector output capacitance	C _{ob}	V _{CB} =- 10V, I _E =0, f=1kHz			3.5	pF
Noise figure	NF	V _{CE} =- 6V, I _C =- 0.1mA, f=1kHz, R _g =10kΩ			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR
Range	70- 140	120- 240	200- 400

Typical Characteristics

